

| Reg.No | 19BEC0358 | | |
|---------------|--------------------|-----------------|----------------|
| Student Name | ARPIT PATAWAT | | |
| Course Code | ECE3002 | Slot & Semester | L43+L44 |
| | | | WINTER 2021-22 |
| Course Name | VLSI system design | | |
| Program Title | Lab Assignment 1 | | |
| Faculty | Dr. Ragunath G | | |

School of Electronics Engineering ,VIT, Vellore

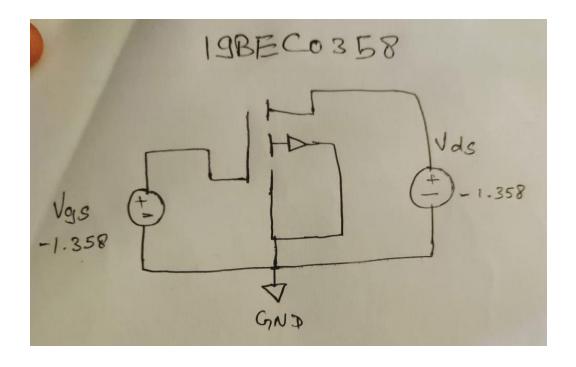
- 1.PlotTransfer characteristics of a PMOS and Determine the threshold voltage (Approximate) of the PMOS.
- 2. Plot Drain characteristics of a PMOS and Determine the operating regions (Approximate) of the PMOS.
- 3. Determine the channel length modulation parameter (λ)from saturation region of the PMOS.
- 4. Show the body effect of the PMOS with different VsB.

1.

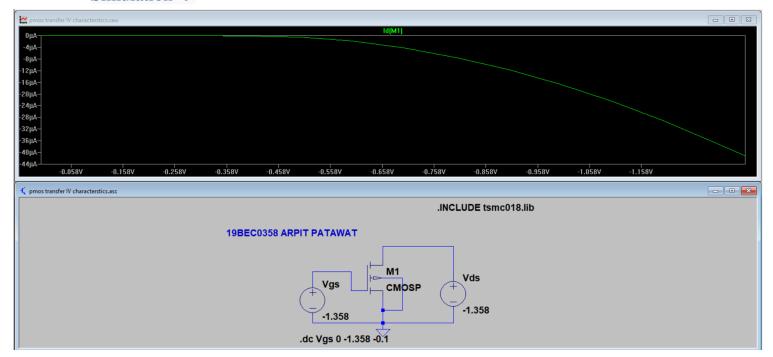
Aim → to plot transfer characteristics of PMOS and determine threshold voltage

Circuit Diagram → Width = length = 180 nm

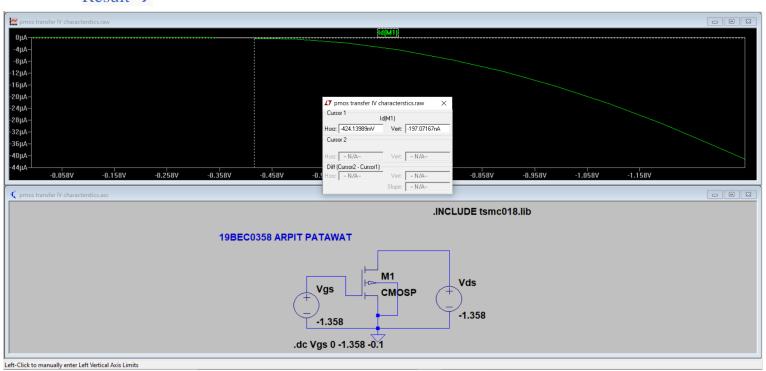
.INCLUDE tsmc018.lib 19BEC0358 ARPIT PATAWAT Vgs CMOSP -1.358 -1.358 .dc Vgs 0 -1.358 -0.1



Simulation \rightarrow



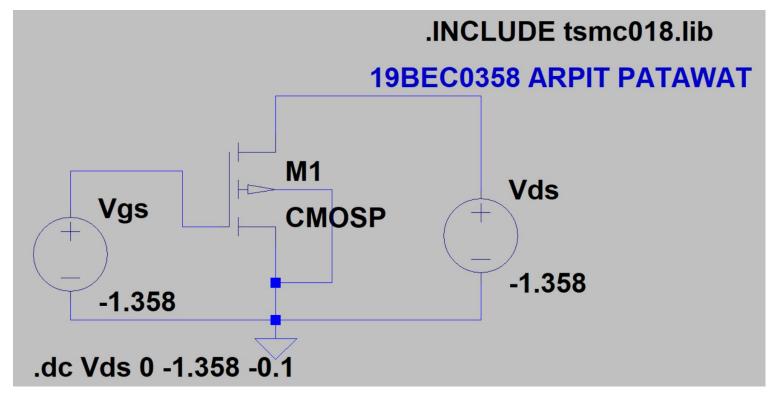
Result →



Graph b/w Vgs and Id

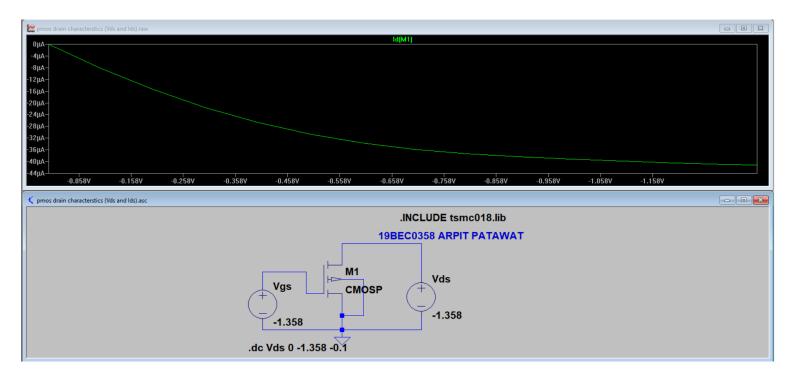
Threshold value → -0.424V

Aim → to plot Drain characteristics of PMOS and determine Operating Regions of PMOS



Circuit Diagram →

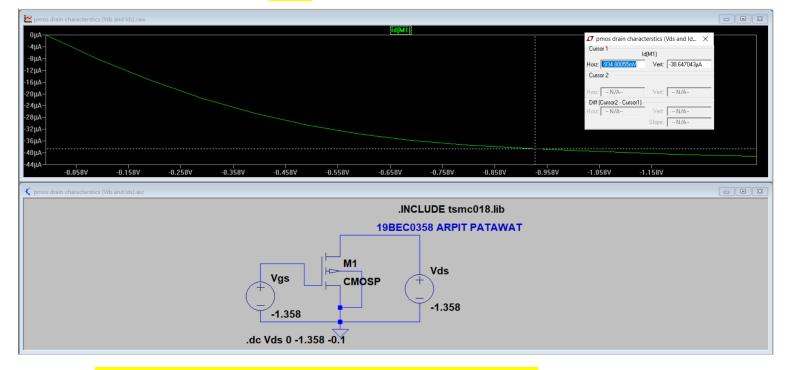
Simulation \rightarrow



Graph b/w Vds and Id

Result \rightarrow When Vds = Vgs – Vt \rightarrow transistor goes to saturation

 $Vds = -1.358 - (-0.424v) \rightarrow -0.934V$

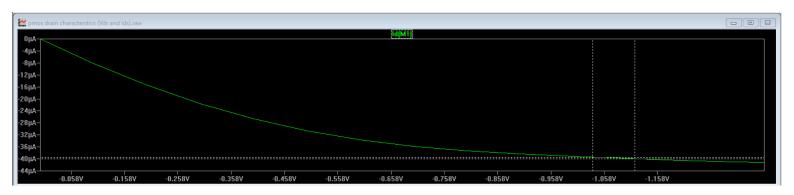


Left side of mark of -0.934 is linear mode and right part is saturation mode.

3

Aim → to determine the channel length modulation parameter from saturation region of PMOS

Circuit Diagram →



Here we have to take 2 points from the saturation region of drain characteristic of PMOS from which we will get absolute vds1, vds2 and corresponding absolute current ids1 and ids2 and these values are used to find the channel length modulation of PMOS from saturation region of PMOS.

$$I_{d1} = \frac{\beta (v_{gs} - v_t)^2 (1 + \lambda v_{ds1})}{2}$$
 ----- Eq 1

$$I_{d2} = \frac{\beta (v_{gs} - v_t)^2 (1 + \lambda v_{ds2})}{2}$$
 ----- Eq 2

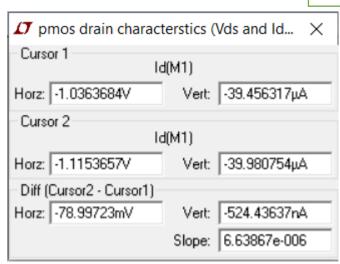
Eq
$$2 / \text{Eq } 1 \rightarrow$$

$$\frac{I_{d2}}{I_{d1}} = \frac{(1 + \lambda * v_{ds2})}{(1 + \lambda * v_{ds1})}$$

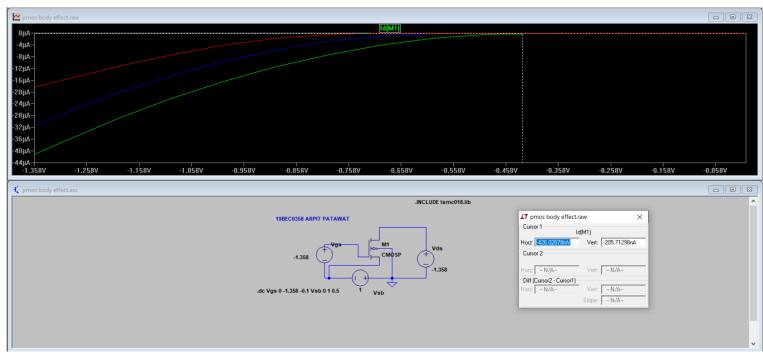
$$\frac{39.980}{39.456} = \frac{(1 + \lambda * 1.115)}{(1 + \lambda * 1.036)}$$

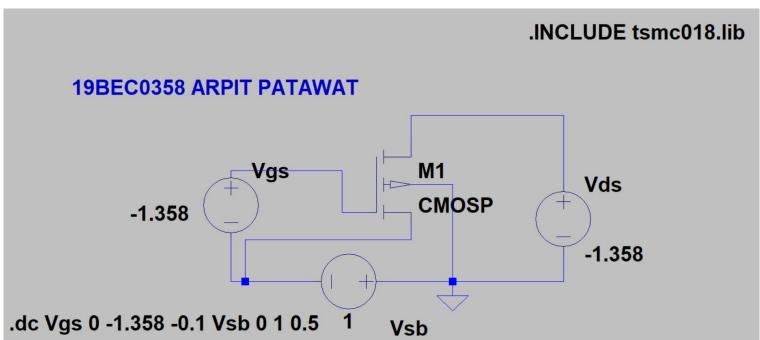
$$1.013*(1 + \lambda * 1.036) = (1 + \lambda * 1.115)$$

$$\lambda * (1.049 - 1.115) = 1 - 1.013 \rightarrow \lambda = 0.196 \text{ V}^{-1}$$



4
Aim → to Show body effect of PMOS with different Vsb
Circuit Diagram →





As we keep on increasing Vsb, threshold voltage increase. This is body effect of PMOS.